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Customer No.: 31561 Docket No.: 12278-US-PA

Application No.: 10/711,002

AMENDMENTS

To the Claims:

Please amend the claims according to the following listing of claims and substitute it for

all prior versions and listings of claims in the application.

Claim 1 (currently amended) A white light light emitting diode (LED), comprising:

an exciting light source, for emitting a light having a wavelength in a range of about

250nm to about 350490nm; and

fluorescent powders, disposed around the exciting light source, comprising yellow-light

fluorescent materials and at least two three different fluorescent materials selected from a group

consisting of yellow-light fluorescent materials, red-light fluorescent materials, green-light

fluorescent materials, and blue-light fluorescent materials.

Claim 2 (cancelled)

Claim 3 (currently amended) The white light LED of claim 1, wherein when the

wavelength of the light is in a range of about 250nm to about 440nm, the material of the

fluorescent powder includes yellow-light fluorescent materials selected from a group consisting

of (Tb_{3-x-y}Ce_xRe_y)Al₅O₁₂, (Me_{1-x-y}Eu_xRe_y)₃SiO₅, Y₂O₃:Eu³⁺, YBO₃:Ce³⁺, green-light fluorescent

materials selected from a group consisting of YBO3:TB3+, SrGa2O4:Eu2+, SrAl2O4:Eu2+,

 $(Ba,Sr)MgAl_{10}O_{17}:Eu^{2+},\ (Ba,Sr)MgAl_{10}O_{17}:Mn^{2+},\ red-light\ fluorescent\ materials\ selected\ from\ a$ group consisting of $Y_2O_3:Eu^{3+},\ Y_2O_3:Bi^{3+},\ (Y,Gd)_2O_3:Eu^{3+},\ (Y,Gd)_2O_3:Bi^{3+},\ Y_2O_2S:Eu^{3+},$ $Y_2O_2S:Eu^{3+},\ (Y_2O_2S:Bi^{3+},(Me_{1-x}Eu_x)ReS,\ 6MgO_1As_2O_5:Mn,\ Mg_3SiO_4:Mn,\ and\ blue-light\ fluorescent\ materials$ selected from a group consisting of $BaMgAl_{10}O_{17}:Eu^{2+},\ (Ca,Sr,Ba)_5(PO_4)_3Cl:Eu^{2+},Gd^{2+}.$

Claim 4 (currently amended) The white light LED of claim 31, wherein $0 < x \le 0.8$ and $0 \le y \le 2.0$.

Claim 5 (currently amended) The white light LED of claim 34, wherein Me comprises calcium, strontium, or barium.

Claim 6 (currently amended) The white light LED of claim 34, wherein Re comprises praseodymium (Pr), rubidium, samarium (Sm), dysprosium (Dy), holmium (Ho), yttrium, erbium (Er), europium (Eu), thulium (Tm), ytterbium (Yb), chromium, strontium, lutetium (Lu), gadolinium (Gd), aluminum, or zinc.

Claim 7 (original) The white light LED of claim 1, wherein the exciting light source comprises LED chip or laser diode chip.

Claim 8 (currently amended) A white light light emitting diode (LED), comprising: a susceptor, having a pit in a surface of the susceptor;

an exciting light source, disposed in the pit of the susceptor and electrically connected to the susceptor, wherein a light having a wavelength in a range of about 250nm to about 350490nm is emitted from the exciting light source;

a sealing resin, disposed over the susceptor, wherein the exciting light source is covered by the sealing resin to mount the exciting light source over the susceptor; and

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fluorescent powders, disposed around the exciting light source, comprising yellow-light fluorescent materials and at least two three different fluorescent materials selected from a group consisting of <u>yellow-light fluorescent materials</u>, red-light fluorescent materials, green-light fluorescent materials, and blue-light fluorescent materials.

Claim 9 (original) The white light LED of claim 8, further comprising:

a plurality of welding wire, electrically connected between the exciting light source and the susceptor.

Claim 10 (original) The white light LED of claim 8, wherein the susceptor comprises a packaging leadframe or a circuit board.

Claim 11 (original) The white light LED of claim 8, wherein the exciting light source comprises a LED chip or a laser diode chip.

Claim 12 (cancelled)

Claim 13 (currently amended) The white light LED of claim 8, wherein when the wavelength of the light is in a range of about 250nm to about 440nm, the material of the fluorescent powder includes yellow-light fluorescent materials selected from a group consisting of (Tb_{3-x-y}Ce_xRe_y)Al₅O₁₂, (Me_{1-x-y}Eu_xRe_y)₃SiO₅, Y₂O₃:Eu³⁺, YBO₃:Ce³⁺, green-light fluorescent materials selected from a group consisting of YBO₃:TB³⁺, SrGa₂O₄:Eu²⁺, SrAl₂O₄:Eu²⁺, (Ba,Sr)MgAl₁₀O₁₇:Eu²⁺, (Ba,Sr)MgAl₁₀O₁₇:Mn²⁺, red-light fluorescent materials selected from a group consisting of Y₂O₃:Eu³⁺, Y₂O₃:Eu³⁺, (Y,Gd)₂O₃:Eu³⁺, (Y,Gd)₂O₃:Bi³⁺, Y₂O₂S:Eu³⁺,

Y₂O₂S:Bi³⁺,(Me_{1-x}Eu_x)ReS, 6MgO,As₂O₅:Mn, Mg₃SiO₄:Mn, and blue-light fluorescent materials selected from a group consisting of BaMgAl₁₀O₁₇:Eu²⁺, (Ca,Sr,Ba)₅(PO₄)₃Cl:Eu²⁺,Gd²⁺.

Claim 14 (currently amended) The white light LED of claim 138, wherein $0 \le x \le 0.8$, and $0 \le y \le 2.0$.

Claim 15 (currently amended) The white light LED of claim 138, wherein Me comprises calcium, strontium, or barium.

Claim 16 (currently amended) The white light LED of claim 138, wherein Re comprises praseodymium (Pr), rubidium, samarium (Sm), dysprosium (Dy), holmium (Ho), yttrium, erbium (Er), europium (Eu), thulium (Tm), ytterbium (Yb), chromium, strontium, lutetium (Lu), gadolinium (Gd), aluminum, or zinc.

Claim 17 (currently amended) A white light light emitting diode (LED), at least comprising:

a LED chip, for emitting a light having a wavelength in a range of about 250nm to about 350490nm, wherein the LED chip comprising:

a substrate;

an nucleation layer, disposed over the substrate;

a conductive buffer layer, disposed over the nucleation layer;

a first confinement layer, disposed over the conductive buffer layer, wherein a type of a (conductive) doping material of the first confinement layer and a type of a (conductive) doping material of the conductive buffer layer are the same;

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a light emitting layer, disposed over the first confinement layer, wherein the light

emitting layer comprises doped III-V compound semiconductor material;

a second confinement layer, disposed over the light emitting layer, wherein a type of the

(conductive) doping material of the second confinement layer and the type of the (conductive)

doping material of the first confinement layer are different;

a contact layer, disposed over the second confinement layer, wherein the contact layer

comprises a superlattice structure material layer;

an anode electrode, disposed over the contact layer;

a cathode electrode, contacted to the conductive buffer layer, and isolated from the first

and the second confinement layer, the light emitting layer, the contact layer and the anode

electrode; and

fluorescent powders, disposed around the exciting light source, comprising yellow-light

fluorescent materials and at least two three different fluorescent materials selected from a group

consisting of vellow-light fluorescent materials, red-light fluorescent materials, green-light

fluorescent materials, and blue-light fluorescent materials.

Claim 18 (cancelled)

Claim 19 (currently amended) The white light LED of claim 17, wherein when the

wavelength of the light is in a range of about 250nm to about 440nm, the material of the

fluorescent powder includes yellow-light fluorescent materials selected from a group consisting

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of $(Tb_{3-x-y}Ce_xRe_y)Al_5O_{12}$, $(Me_{1-x-y}Eu_xRe_y)_3SiO_5$, $\underline{Y_2O_3:Eu^{3+}}$, $\underline{YBO_3:Ce^{3+}}$, green-light fluorescent materials selected from a group consisting of $\underline{YBO_3:TB^{3+}}$, $\underline{SrGa_2O_4:Eu^{2+}}$, $\underline{SrAl_2O_4:Eu^{2+}}$, $(Ba_sSr)MgAl_{10}O_{17}:Eu^{2+}$, $(Ba_sSr)MgAl_{10}O_{17}:Mn^{2+}$, red-light fluorescent materials selected from a group consisting of $\underline{Y_2O_3:Eu^{3+}}$, $\underline{Y_2O_3:Bi^{3+}}$, $(\underline{Y_sGd})_2O_3:\underline{Eu^{3+}}$, $(\underline{Y_sGd})_2O_3:\underline{Bi^{3+}}$, $\underline{Y_2O_2S:Eu^{3+}}$, $\underline{Y_2O_2S:Bi^{3+}}$, $\underline{Me_{1-x}Eu_x}ReS$, $\underline{6MgO_sAs_2O_5:Mn}$, $\underline{Mg_3SiO_4:Mn}$, and $\underline{blue-light}$ fluorescent materials selected from a group consisting of $\underline{BaMgAl_{10}O_{17}:Eu^{2+}}$, $\underline{(Ca_sSr_sBa)_5(PO_4)_3Cl:Eu^{2+}}$, $\underline{Gd^{2+}}$.

Claim 20 (currently amended) The white light LED of claim 1917, wherein $0 \le x \le 0.8$ and $0 \le y \le 2.0$.

Claim 21 (currently amended) The white light LED of claim 1917, wherein Me comprises calcium, strontium or barium.

Claim 22 (currently amended) The white light LED of claim 1917, wherein Re comprises praseodymium (Pr), rubidium, samarium (Sm), dysprosium (Dy), holmium (Ho), yttrium, erbium (Er), europium (Eu), thulium (Tm), ytterbium (Yb), chromium, strontium, lutetium (Lu), gadolinium (Gd), aluminum or zinc.

Claim 23 (original) The white light LED of claim 17, wherein a super high conductivity material of the contact layer comprises strained layer superlattice (SLS) material.

Claim 24 (original) The white light LED of claim 23, wherein a conductive type of the contact layer and a conductive type of the second confinement layer are different.

Claim 25 (original) The white light LED of claim 23, wherein a conductive type of the contact layer and a conductive type of the anode electrode are different.

Claim 26 (original) The white light LED of claim 17, wherein the anode electrode comprises a conventional metal used in a semiconductor process and a multi-layer structure composed of a mixture of the conventional metal, wherein a total thickness of the anode electrode is equal to or less than 0.1 µm.

Claim 27 (original)The white light LED of claim 26, wherein the anode electrode comprises a transparent conductive oxide (TCO), wherein the TCO comprises a N-type conductive material comprising indium tin oxide (ITO), cadmium tin oxide (CTO), ZnO:Al, ZnO:In, ZnO:Ga, ZnGa₂O₄, SnO₂:Sb, Ga₂O₃:Sn, AgInO₂:Sn and In₂O₃:Zn, or a P-type conductive material comprising CuAlO₂, LaCuOS, NiO, CuGaO₂ and SrCu₂O₂.

Claim 28 (currently amended) The white light LED of claim 17, wherein the substrate is comprised aluminum oxide, sapphire, silicon sileon carbide (SiC), zinc oxide (ZnO), silicon substrate, gallium phosphide (GaP) or gallium arsenide (GaAs).

Claim 29 (original) The white light LED of claim 17, wherein the light emitting layer comprises a doped III-V compound semiconductor quantum well structure.

Claim 30 (original) The white light LED of claim 29, wherein the quantum well structure comprises doped III-V compound semiconductor comprising $Al_0In_bGa_{1-a-b}N/Al_xIn_yGa_{1-x-y}N$, wherein $a,b\geq 0$; $0\leq a+b<1$; $x,y\geq 0$; $0\leq x+y<1$; x>c>a.

Claim 31 (original) The white light LED of claim 17, wherein the cathode electrode comprises Cr/Au, Cr/Pt/Au, Cr/WSiN/Au, WSi_x/Au, Ti/Si_x/Au, Ti/Au, Ti/WSi_x/Au, Ti/Al/Cr/Au, Ti/Al/Cr/Au, Cr/Al/Cr/Au, Cr/Al/Pt/Au, Cr/Al/Pd/Au, Cr/Al/Ti/Au, Cr/Al/Co/Au, Cr/Al/Ni/Au, Pd/Al/Ti/Au, Pd/Al/Pt/Au, Pd/Al/Ni/Au, Pd/Al/Pd/Au, Pd/Al/Cr/Au, Pd/Al/Co/Au,

Nd/Al/Pt/Au, Nd/Al/Ti/Au, Nd/Al/Ni/Au, Nd/Al/Cr/Au Nd/Al/Co/A, Hf/Al/Ti/Au, Hf/Al/Pt/Au, Hf/Al/Pt/Au, Hf/Al/Pt/Au, Hf/Al/Pt/Au, Hf/Al/Pt/Au, Hf/Al/Pt/Au, Zr/Al/Pt/Au, Zr/Al/Pt/Au, Zr/Al/Pt/Au, Zr/Al/Ni/Au, Zr/Al/Pt/Au, Zr/Al/Cr/Au, Zr/Al/Co/Au, TiNx/Ti/Au, TiNx/Pt/Au, TiNx/Ni/Au, TiNx/Pd/Au, TiNx/Cr/Au, TiNx/Co/Au TiWNx/Ti/Au, TiWNx/Pt/Au, TiWNx/Ni/Au, TiWNx/Pd/Au, TiWNx/Cr/Au, TiWNx/Co/Au, NiAl/Pt/Au, NiAl/Cr/Au, NiAl/Ni/Au, NiAl/Ti/Au, Ti/NiAl/Pt/Au, Ti/NiAl/Pt/Au, Ti/NiAl/Ti/Au, Ti/NiAl/Pt/Au, Ti/NiAl/Ti/Au, Ti/NiAl/Ti/Au, Ti/NiAl/Ni/Au or Ti/NiAl/Cr/Au.